

## Features

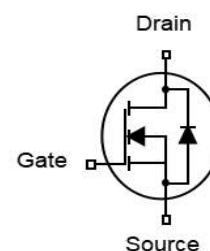
- N-Channel
- Low  $R_{DS(ON)}$  & FOM
- Extremely low switching loss
- Excellent reliability and uniformity
- Fast switching and soft recovery
- 100% EAS Tested

$V_{DS}$	40	V
$R_{DS(on),TYP@ V_{GS}=10V}$	1.0	m $\Omega$
$R_{DS(on),TYP@ V_{GS}=4.5V}$	1.5	m $\Omega$
$I_D$	160	A

DFN5x6



Part ID	Package Type	Marking	Packing
ZTG010N04GC	DFN5x6	ZTG010N04GC	5000pcs/Reel



## Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ , unless otherwise specified

Symbol	Parameter	Rating	Unit	
<b>Common Ratings (<math>T_C = 25^\circ\text{C}</math> Unless Otherwise Noted)</b>				
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V	
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	40	V	
$T_J$	Maximum Junction Temperature	150	$^\circ\text{C}$	
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$	
$I_{DM}$	Drain Current-Continuous@ Current-Pulsed (Note 1)	$T_C = 25^\circ\text{C}$ 640	A	
<b>Mounted on Large Heat Sink</b>				
$I_D$	Drain Current-Continuous	$T_C = 25^\circ\text{C}$	160	A
		$T_C = 100^\circ\text{C}$	115	A
$P_D$	Maximum Power Dissipation (Note 2)	140	W	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	0.89	$^\circ\text{C/W}$	
$R_{\theta JA}$	Thermal Resistance Junction-Ambient (Note 3)	48	$^\circ\text{C/W}$	
<b>Drain-Source Avalanche Ratings</b>				
EAS	Avalanche Energy, Single Pulsed (Note 7)	562	mJ	

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Condition	Min	Typ	Max	Unit
<b>Static Electrical Characteristics @ T<sub>J</sub>=25°C (unless otherwise stated)</b>						
V(BR)DSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	40	--	--	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V	--	--	1	μA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	--	--	±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.4	1.9	2.4	V
R <sub>DS(on)</sub>	Drain-Source On-State Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =50A	--	1.0	1.2	mΩ
R <sub>DS(on)</sub>	Drain-Source On-State Resistance	V <sub>GS</sub> =4.5V, I <sub>D</sub> =45A	--	1.5	1.9	mΩ
<b>Dynamic Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise stated) (Note 5)</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V, f=1MHz	--	5968	--	pF
C <sub>oss</sub>	Output Capacitance		--	2451	--	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		--	119	--	pF
R <sub>g</sub>	Gate Resistance	f=1MHz	--	--	5	Ω
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =20V, I <sub>D</sub> =50A, V <sub>GS</sub> =10V	--	85	--	nC
Q <sub>gs</sub>	Gate-Source Charge		--	25	--	nC
Q <sub>gd</sub>	Gate-Drain Charge		--	7.9	--	nC
<b>Switching Characteristics (Note 5)</b>						
T <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DD</sub> =20V, I <sub>D</sub> =50A, R <sub>G</sub> =4.0Ω, V <sub>GS</sub> =10V	--	19	--	ns
T <sub>r</sub>	Turn-on Rise Time		--	62	--	ns
T <sub>d(off)</sub>	Turn-Off Delay Time		--	84	--	ns
T <sub>f</sub>	Turn-Off Fall Time		--	27	--	ns
<b>Source- Drain Diode Characteristics @ T<sub>J</sub> = 25°C (unless otherwise stated)</b>						
I <sub>S</sub>	Diode Forward Current (Note 3)		--	--	160	A
V <sub>SD</sub>	Forward on voltage (Note 6)	I <sub>S</sub> =160A, V <sub>GS</sub> =0V	--	--	1.4	V
T <sub>rr</sub>	Reverse Recovery Time (Note 4)	T <sub>J</sub> =25°C, I <sub>F</sub> =50A di/dt=100A/μs	--	82	--	ns
Q <sub>rr</sub>	Reverse Recovery Charge		--	99	--	nC

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub> = 25° C.
2. The power dissipation PD is based on T<sub>J</sub>(MAX)=150°C, using junction-to-case thermal resistance.
3. Surface Mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub> = 25°C.
4. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
5. Guaranteed by design, not subject to production.
6. The maximum current limited by package
7. EAS condition : T<sub>J</sub>=25°C, V<sub>DD</sub>=20V, V<sub>G</sub>=10V, L=0.5mH, R<sub>G</sub>=25Ω

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

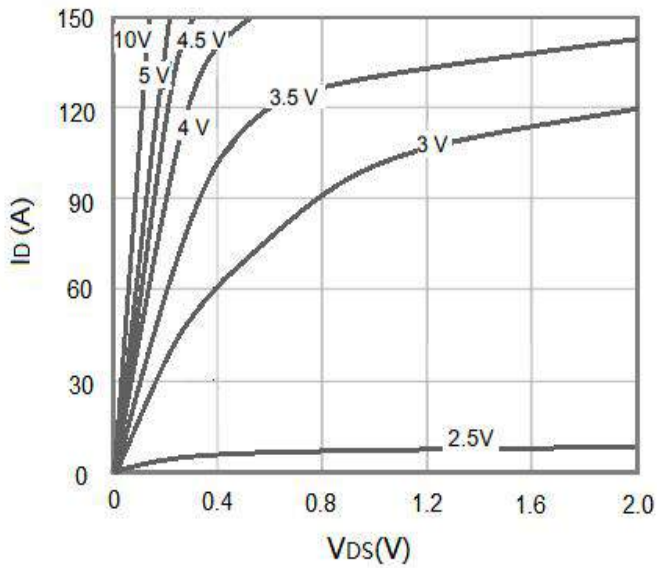


Figure 1 Output Characteristics

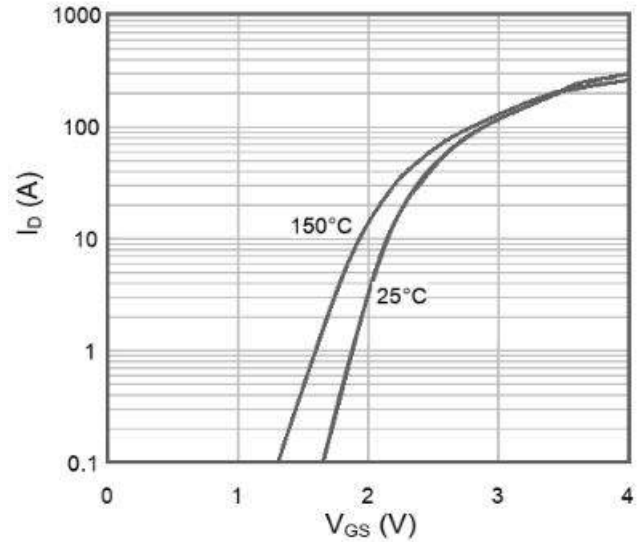


Figure 4 Transfer Characteristics

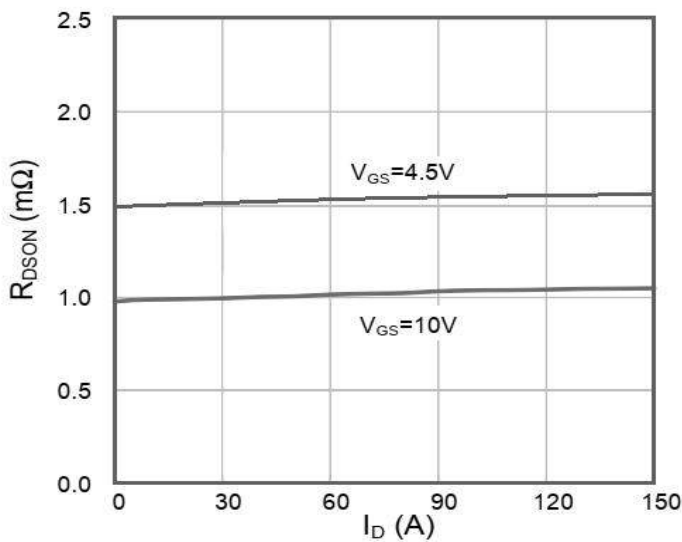


Figure 2 Rdson- Drain Current

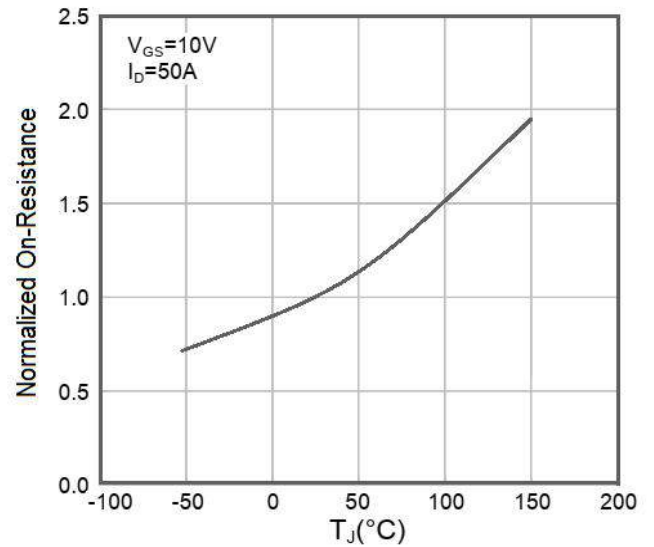


Figure 5 Rdson-Junction Temperature

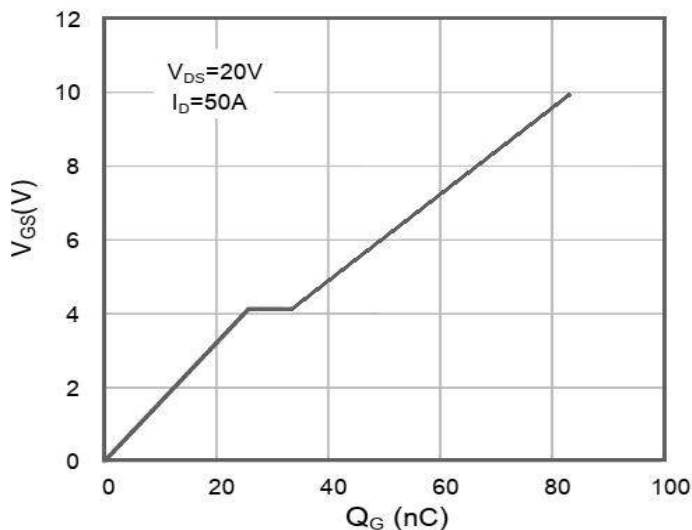


Figure 3 Gate Charge

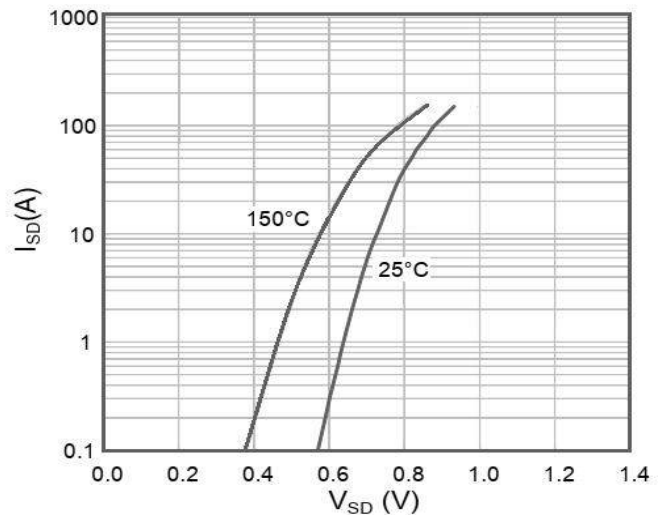


Figure 6 Source- Drain Diode Forward

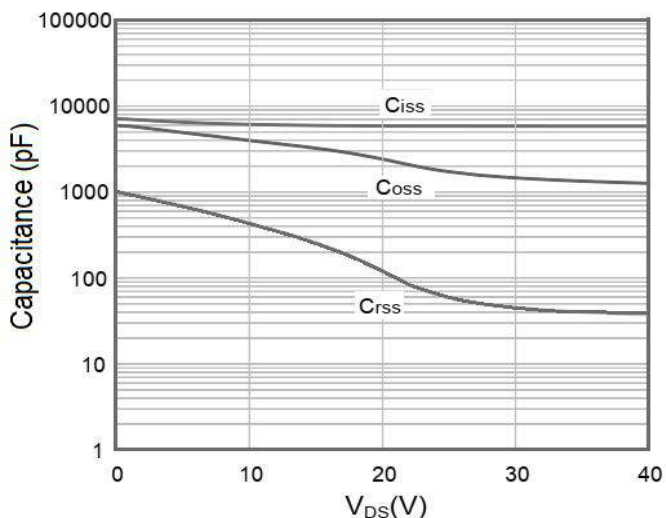


Figure 7 Capacitance vs Vds

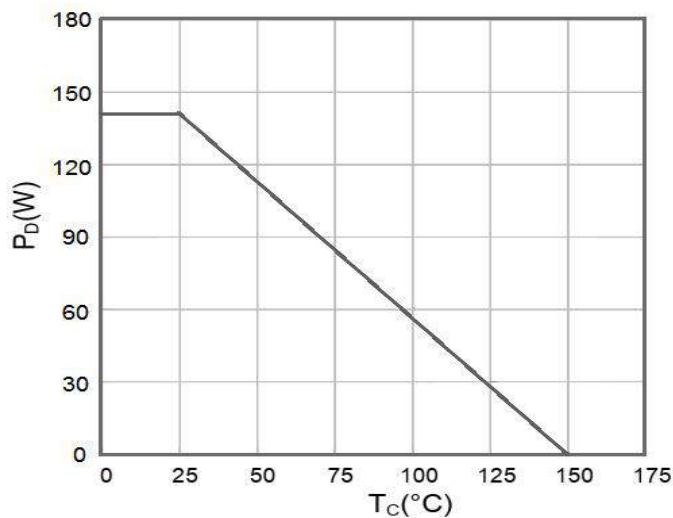


Figure 9 Power De-rating

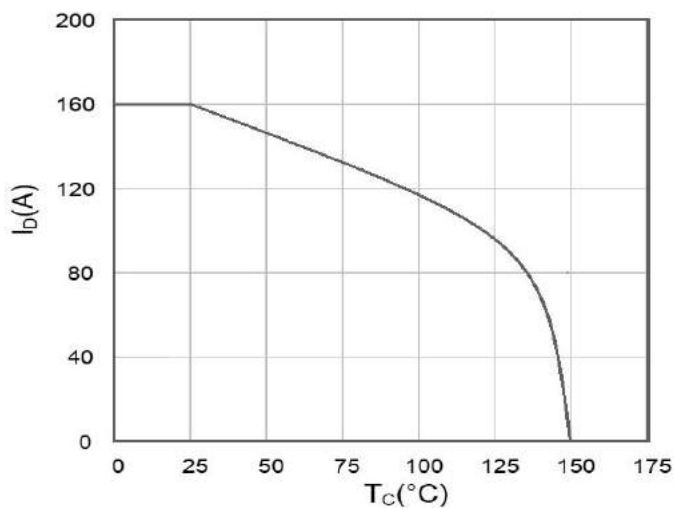


Figure 8 Current De-rating

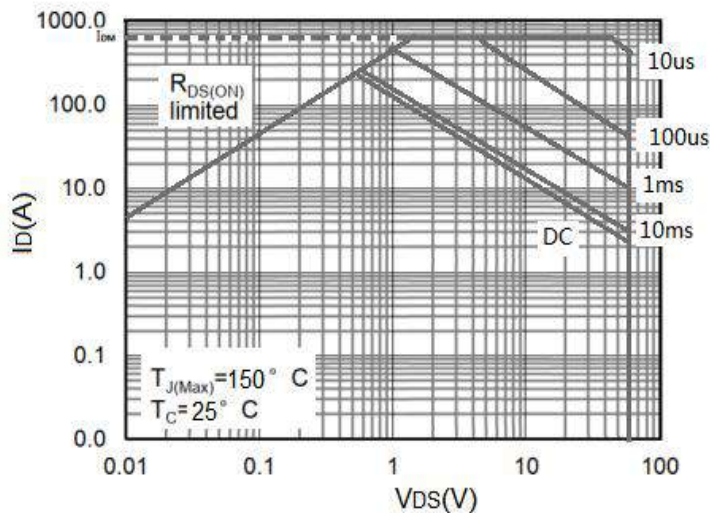


Figure 10 Safe Operation Area

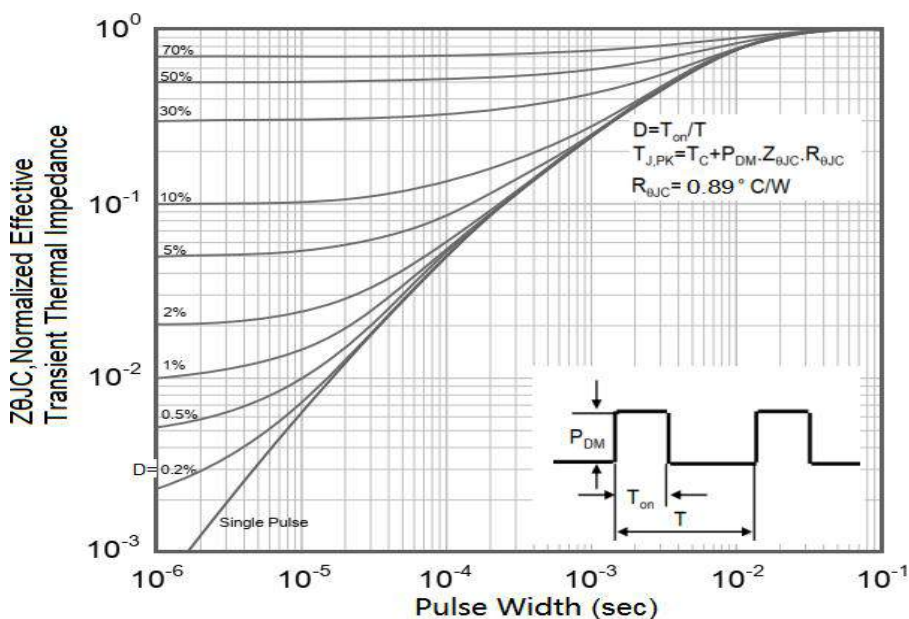
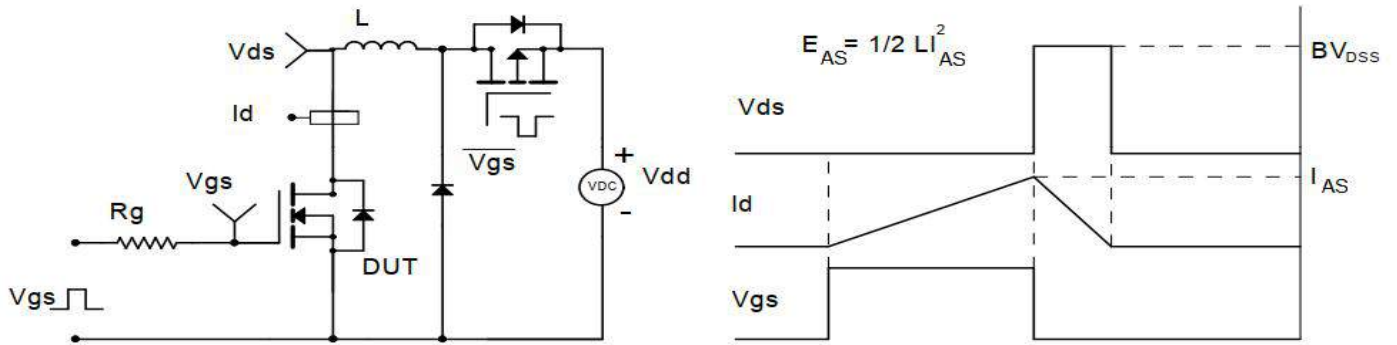


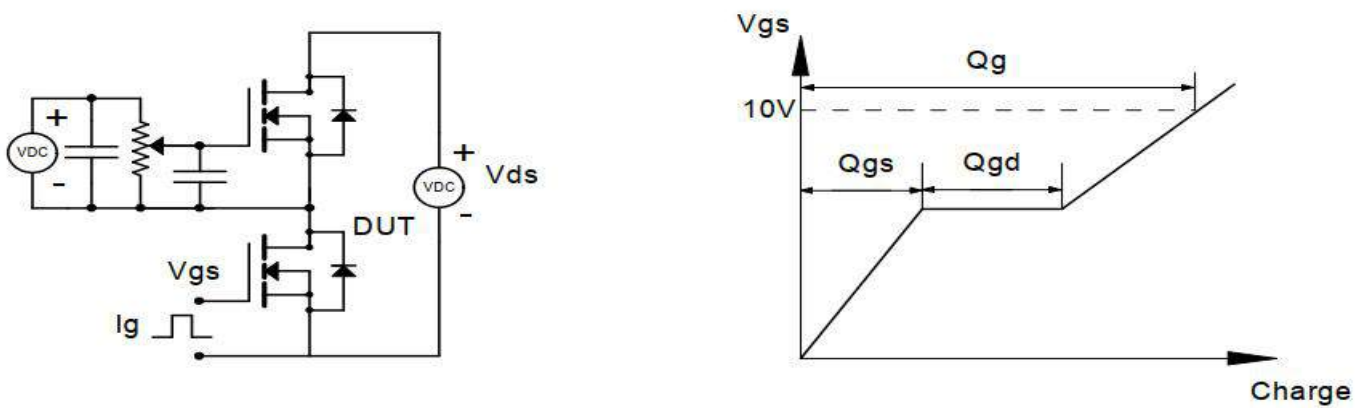
Figure 11 Normalized Maximum Transient Thermal Impedance

Test circuit&Waveform

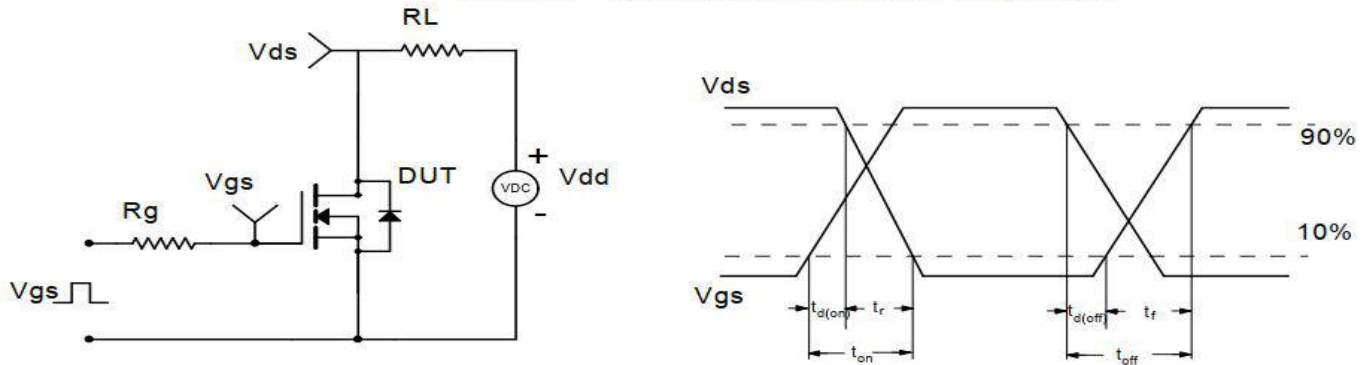
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



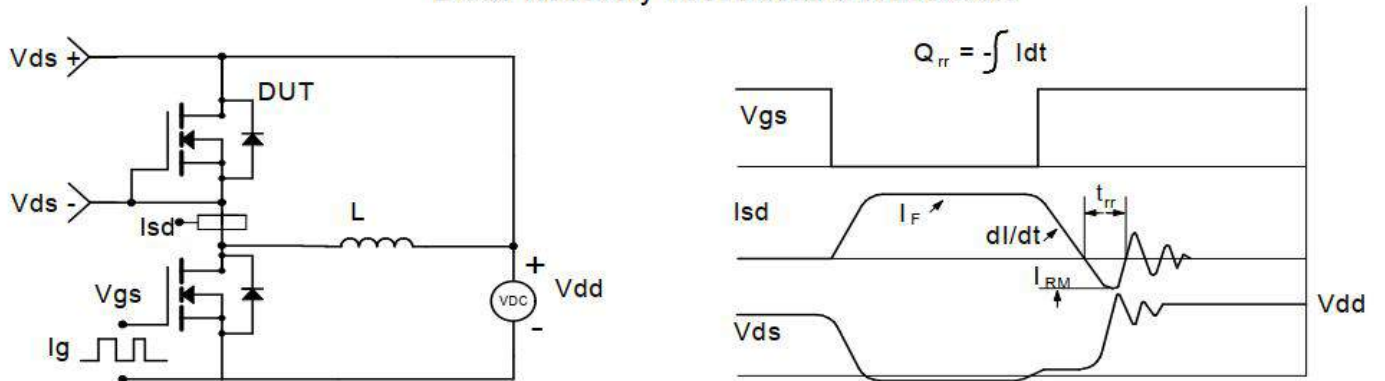
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

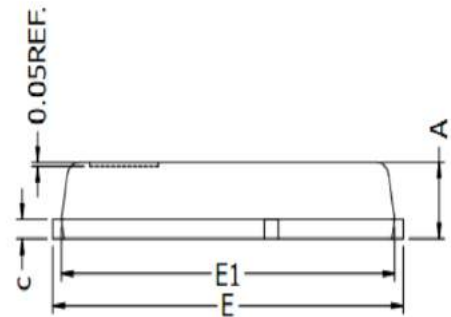
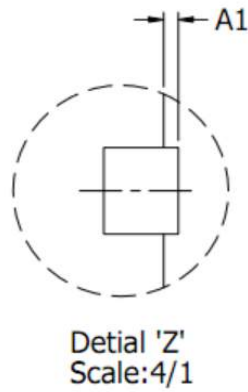
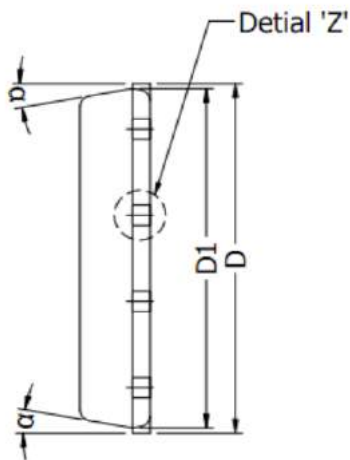
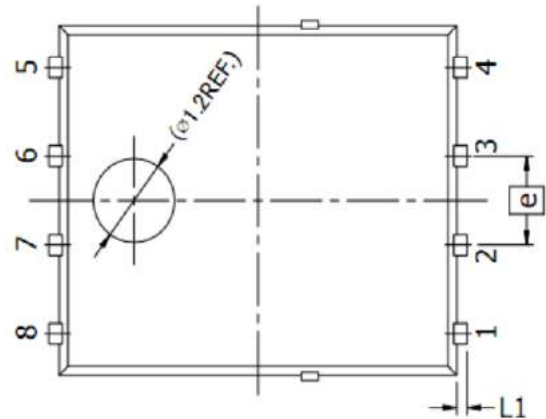
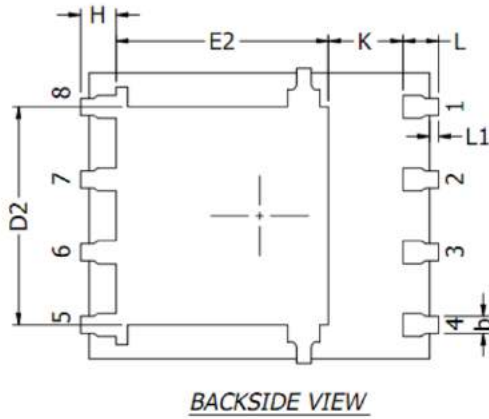


Diode Recovery Test Circuit & Waveforms





## DFN5x6-8L Package Information



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.30	0.40	0.50
c	0.20	0.25	0.30
D	5.15 BSC		
D1	5.00 BSC		
D2	3.76	3.81	3.86
E	6.15 BSC		
E1	5.80	5.85	5.90
E2	3.45	3.65	3.85
e	1.27 BSC		
H	0.51	0.61	0.71
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.08	0.15	0.23
α	10°	11°	12°

## Customer Service

Sales and Service:  
[zj@ztasemi.com](mailto:zj@ztasemi.com)